Matteo Meneghini

List of Publications by Year
in descending order

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485	11,552	50	89
papers	citations	h-index	g-index

44444 53065

489	489	489	6038
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Cumulative Hot-Electron Trapping in GaN-Based Power HEMTs Observed by an Ultrafast (10 V/Ns) On-Wafer Methodology. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2022, 10, 5019-5026.	3.7	15
2	Origin of the Diffusion-Related Optical Degradation of 1.3 Î¼m Inas QD-LDs Epitaxially Grown on Silicon Substrate. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-9.	1.9	6
3	Laser-induced activation of Mg-doped GaN: quantitative characterization and analysis. Journal Physics D: Applied Physics, 2022, 55, 185104.	1.3	3
4	Photon-induced degradation of InGaN-based LED in open-circuit conditions investigated by steady-state photocapacitance and photoluminescence. Journal of Applied Physics, 2022, 131, .	1.1	3
5	Trap-state mapping to model GaN transistors dynamic performance. Scientific Reports, 2022, 12, 1755.	1.6	10
6	Defects and Reliability of GaNâ€Based LEDs: Review and Perspectives. Physica Status Solidi (A) Applications and Materials Science, 2022, 219, .	0.8	28
7	Reliability of Commercial UVC LEDs: 2022 State-of-the-Art. Electronics (Switzerland), 2022, 11, 728.	1.8	20
8	Modeling the effect of spatial position and concentration of defects on optical degradation of InGaN/GaN multi quantum well light emitting diodes. , 2022, , .		0
9	Role of carbon in dynamic effects and reliability of 0.15-um AlGaN/GaN HEMTs for RF power amplifiers. , 2022, , .		1
10	UV LED reliability: degradation mechanisms and challenges. , 2022, , .		2
11	Failure Physics and Reliability of GaNâ€Based HEMTs for Microwave and Millimeterâ€Wave Applications: A Review of Consolidated Data and Recent Results. Physica Status Solidi (A) Applications and Materials Science, 2022, 219, .	0.8	6
12	Conduction properties and threshold voltage instability in Î²-Ga2O3 MOSFETs. , 2022, , .		2
13	GaN-based solar cells degradation kinetics investigated at high temperature under high-intensity 405nm optical stress. , 2022, , .		1
14	Analysis and design of SARS-CoV-2 disinfection chambers based on UVC LEDs. , 2022, , .		0
15	Optical degradation of InAs quantum-dot lasers on silicon: dependence on temperature and on diffusion processes. , 2022, , .		0
16	Defects in III-N LEDs: experimental identification and impact on electro-optical characteristics. , 2022, , .		0
17	Investigation of deep level defects in n-type GaAsBi. , 2022, , .		0
18	Deep levels and conduction processes in nitrogen-implanted Ga2O3 Schottky barrier diodes. , 2022, , .		0

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19	On the performance and reliability of state-of-the-art commercial UV-C LEDs for disinfection purposes. , 2022, , .		0
20	Deep defects in InGaN LEDs: modeling the impact on the electrical characteristics. , 2022, , .		0
21	Study and characterization of GaN MOS capacitors: Planar vs trench topographies. Applied Physics Letters, 2022, 120, .	1.5	3
22	Logarithmic trapping and detrapping in <i>Î²</i> -Ga2O3 MOSFETs: Experimental analysis and modeling. Applied Physics Letters, 2022, 120, .	1.5	8
23	Influence of Drain and Gate Potential on Gate Failure in Semi-Vertical GaN-on-Si Trench MOSFETs. , 2022, , .		1
24	Deep level effects and degradation of 0.15 Î¼m RF AlGaN/GaN HEMTs with Mono-layer and Bi-layer AlGaN backbarrier. , 2022, , .		0
25	GaN RF HEMT Reliability: Impact of Device Processing on I-V Curve Stability and Current Collapse. , 2022, , .		1
26	Modeling Hot-Electron Trapping in GaN-based HEMTs. , 2022, , .		1
27	Quantum efficiency of InGaNâ€"GaN multi-quantum well solar cells: Experimental characterization and modeling. Journal of Applied Physics, 2022, 131, .	1.1	4
28	Compact Modeling of Nonideal Trapping/Detrapping Processes in GaN Power Devices. IEEE Transactions on Electron Devices, 2022, 69, 4432-4437.	1.6	2
29	Degradation of 1.3 Î¼m InAs Quantum-Dot Laser Diodes: Impact of Dislocation Density and Number of Quantum Dot Layers. IEEE Journal of Quantum Electronics, 2021, 57, 1-8.	1.0	12
30	Full Optical Contactless Thermometry Based on LED Photoluminescence. IEEE Transactions on Instrumentation and Measurement, 2021, 70, 1-8.	2.4	6
31	Degradation mechanisms of InGaN visible LEDs and AlGaN UV LEDs. , 2021, , 273-312.		6
32	GaN-on-silicon transistors with reduced current collapse and improved blocking voltage by means of local substrate removal. Applied Physics Express, 2021, 14, 036501.	1.1	9
33	Data-driven estimation of change points reveals correlation between face mask use and accelerated curtailing of the first wave of the COVID-19 epidemic in Italy. Infectious Diseases, 2021, 53, 243-251.	1.4	10
34	Gradual Degradation of InGaAs LEDs: Impact on Non-Radiative Lifetime and Extraction of Defect Characteristics. Materials, 2021, 14, 1114.	1.3	9
35	â€œHole Redistributionâ€•Model Explaining the Thermally Activated <i>R</i> _{ON} Stress/Recovery Transients in Carbon-Doped AlGaN/GaN Power MIS-HEMTs. IEEE Transactions on Electron Devices, 2021, 68, 697-703.	1.6	36
36	A Generalized Approach to Determine the Switching Reliability of GaN HEMTs on-Wafer Level. , 2021, , .		4

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37	Understanding the Leakage Mechanisms and Breakdown Limits of Vertical GaN-on-Si p+nâˆ’n Diodes: The Road to Reliable Vertical MOSFETs. Micromachines, 2021, 12, 445.	1.4	12
38	Inactivating SARS-CoV-2 Using 275 nm UV-C LEDs through a Spherical Irradiation Box: Design, Characterization and Validation. Materials, 2021, 14, 2315.	1.3	24
39	Challenges and Perspectives for Vertical GaN-on-Si Trench MOS Reliability: From Leakage Current Analysis to Gate Stack Optimization. Materials, 2021, 14, 2316.	1.3	15
40	A Novel Physics-Based Approach to Analyze and Model <i>E</i>-Mode p-GaN Power HEMTs. IEEE Transactions on Electron Devices, 2021, 68, 1489-1494.	1.6	25
41	Influence of Carbon on pBTI Degradation in GaN-on-Si E-Mode MOSc-HEMT. IEEE Transactions on Electron Devices, 2021, 68, 2017-2024.	1.6	6
42	A Physics-Based Approach to Model Hot-Electron Trapping Kinetics in p-GaN HEMTs. IEEE Electron Device Letters, 2021, 42, 673-676.	2.2	25
43	Identification of dislocation-related and point-defects in III-As layers for silicon photonics applications. Journal Physics D: Applied Physics, 2021, 54, 285101.	1.3	7
44	CdTe solar cells: technology, operation and reliability. Journal Physics D: Applied Physics, 2021, 54, 333002.	1.3	25
45	Deep levels and carrier capture kinetics in n-GaAsBi alloys investigated by deep level transient spectroscopy. Journal Physics D: Applied Physics, 2021, 54, 345109.	1.3	11
46	Schottky Gate Induced Threshold Voltage Instabilities in p-GaN Gate AlGaN/GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2021, 21, 169-175.	1.5	25
47	A new method for CdSexTe1-x band grading for high efficiency thin-absorber CdTe solar cells. Solar Energy Materials and Solar Cells, 2021, 226, 111081.	3.0	17
48	Glass-ceramic composites for high-power white-light-emitting diodes. Ceramics International, 2021, 47, 17986-17992.	2.3	10
49	Electric Field and Self-Heating Effects on the Emission Time of Iron Traps in GaN HEMTs. IEEE Transactions on Electron Devices, 2021, 68, 3325-3332.	1.6	20
50	UV-Based Technologies for SARS-CoV2 Inactivation: Status and Perspectives. Electronics (Switzerland), 2021, 10, 1703.	1.8	30
51	Short term reliability and robustness of ultra-thin barrier, 110Ânm-gate AlN/GaN HEMTs. Microelectronics Reliability, 2021, 123, 114199.	0.9	2
52	Dynamic Performance Characterization Techniques in Gallium Nitride-Based Electronic Devices. Crystals, 2021, 11, 1037.	1.0	4
53	Modeling the electrical characteristics of InGaN/GaN LED structures based on experimentally-measured defect characteristics. Journal Physics D: Applied Physics, 2021, 54, 425105.	1.3	21
54	Effect of indium content and carrier distribution on the efficiency and reliability of InGaN/GaN-based multi quantum well light emitting diode. Microelectronics Reliability, 2021, 126, 114377.	0.9	1

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55	Effects of quantum-well indium content on deep defects and reliability of InGaN/GaN light-emitting diodes with under layer. Journal Physics D: Applied Physics, 2021, 54, 505108.	1.3	11
56	Drain Field Plate Impact on the Hard-Switching Performance of AlGaN/GaN HEMTs. IEEE Transactions on Electron Devices, 2021, 68, 5003-5008.	1.6	8
57	Effects of CdTe selenization on the electrical properties of the absorber for the fabrication of CdSexTe1-x/CdTe based solar cells. Solar Energy, 2021, 227, 8-12.	2.9	8
58	Defect incorporation in In-containing layers and quantum wells: experimental analysis via deep level profiling and optical spectroscopy. Journal Physics D: Applied Physics, 2021, 54, 025108.	1.3	20
59	Vertical 3D gallium nitride field-effect transistors based on fin structures with inverted p-doped channel. Semiconductor Science and Technology, 2021, 36, 014002.	1.0	13
60	Nonequilibrium Greenâ€™s Function Modeling of Trap-Assisted Tunneling in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mi>In</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:msub><mml:mi>Ga</mml:mi><mml:mr mathvariant="normal">N</mml:mi></mml:mrow></mml:math> /GaN Light-Emitting Diodes. Physical Review Applied, 2021, 16, .	1.5	4
61	Vertical GaN devices: Process and reliability. Microelectronics Reliability, 2021, 126, 114218.	0.9	9
62	Charge trapping in 0.1Âµm AlGaN/GaN RF HEMTs: Dependence on barrier properties, voltage and temperature. Microelectronics Reliability, 2021, 126, 114259.	0.9	0
63	Degradation mechanisms of 1.3Âµm C-doped quantum dot lasers grown on native substrate. Microelectronics Reliability, 2021, , 114222.	0.9	1
64	Electrical, optical characterization and degradation of Cu(InGa)Se2 devices with fluorine-doped tin oxide back contact. Microelectronics Reliability, 2021, 126, 114260.	0.9	1
65	Hot electron effects in AlGaN/GaN HEMTs during hard-switching events. Microelectronics Reliability, 2021, 126, 114208.	0.9	3
66	Non-monotonic threshold voltage variation in 4H-SiC metalâ€“oxideâ€“semiconductor field-effect transistor: Investigation and modeling. Journal of Applied Physics, 2021, 130, .	1.1	9
67	Positive and negative charge trapping GaN HEMTs: Interplay between thermal emission and transport-limited processes. Microelectronics Reliability, 2021, 126, 114255.	0.9	7
68	Impact of an AlGaN spike in the buffer in 0.15Âµm AlGaN/GaN HEMTs during step stress. Microelectronics Reliability, 2021, 126, 114318.	0.9	2
69	Failure mechanisms of GaN HEMTs for microwave and millimeter-wave applications: from interdiffusion effects to hot-electrons degradation. , 2021, , .		2
70	Review on the degradation of GaN-based lateral power transistors. E-Prime, 2021, 1, 100018.	2.1	3
71	Analysis of Se Co-evaporation and Post-selenization for Sb₂Se₃-Based Solar Cells. ACS Applied Energy Materials, 2021, 4, 12479-12486.	2.5	13
72	GaN-based power devices: Physics, reliability, and perspectives. Journal of Applied Physics, 2021, 130, .	1.1	191

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73	Understanding the effects of off-state and hard-switching stress in gallium nitride-based power transistors. Semiconductor Science and Technology, 2021, 36, 014001.	1.0	10
74	A Review of the Reliability of Integrated IR Laser Diodes for Silicon Photonics. Electronics (Switzerland), 2021, 10, 2734.	1.8	6
75	Current crowding as a major cause for InGaN LED degradation at extreme high current density. , 2021, , .		0
76	Microstructural Degradation Investigations of OFF-State Stressed 0.15 Î¼m RF AlGaN/GaN HEMTs: Failure Mode related Breakdown. , 2021, , .		0
77	Dynamic and Capacitive Characterization of 3D GaN n-p-n Vertical Fin-FETs. , 2021, , .		0
78	Detrapping Kinetics in N-polar AlGaN/GaN MIS-HEMTs. , 2021, , .		1
79	Impact of thermal annealing on deep levels in nitrogen-implanted Î²-Ga2O3 Schottky barrier diodes. Journal of Applied Physics, 2021, 130, .	1.1	3
80	Charge Trapping in GaN Power Transistors: Challenges and Perspectives. , 2021, , .		4
81	Investigation of Current-Driven Degradation of 1.3 <i>Î¼</i>m Quantum-Dot Lasers Epitaxially Grown on Silicon. IEEE Journal of Selected Topics in Quantum Electronics, 2020, 26, 1-8.	1.9	13
82	Low Onâ€Resistance and Low Trapping Effects in 1200â€‰V Superlattice GaNâ€onâ€Silicon Heterostructures. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900687.	0.8	7
83	Degradation Mechanisms of GaNâ€Based Vertical Devices: A Review. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900750.	0.8	8
84	Vertical breakdown of GaN on Si due to V-pits. Journal of Applied Physics, 2020, 127, .	1.1	24
85	High Breakdown Voltage and Low Buffer Trapping in Superlattice GaN-on-Silicon Heterostructures for High Voltage Applications. Materials, 2020, 13, 4271.	1.3	14
86	Cause and Effects of OFF-State Degradation in Hydrogen-Terminated Diamond MESFETs. IEEE Transactions on Electron Devices, 2020, 67, 4021-4026.	1.6	8
87	The 2020 UV emitter roadmap. Journal Physics D: Applied Physics, 2020, 53, 503001.	1.3	289
88	GaN Vertical pâ€“iâ€“n Diodes in Avalanche Regime: Time-Dependent Behavior and Degradation. IEEE Electron Device Letters, 2020, 41, 1300-1303.	2.2	3
89	Excitation Intensity and Temperature-Dependent Performance of InGaN/GaN Multiple Quantum Wells Photodetectors. Electronics (Switzerland), 2020, 9, 1840.	1.8	13
90	Highly stable threshold voltage in GaN nanowire FETs: The advantages of <i>p</i>-GaN channel/Al2O3 gate insulator. Applied Physics Letters, 2020, 117, .	1.5	15

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91	Surging critical care capacity for COVID-19: Key now and in the future. Progress in Disaster Science, 2020, 8, 100136.	1.4	11
92	GaN-based high-periodicity multiple quantum well solar cells: Degradation under optical and electrical stress. Microelectronics Reliability, 2020, 114, 113802.	0.9	5
93	Charge Trapping and Stability of E-Mode p-gate GaN HEMTs Under Soft- and Hard- Switching Conditions. , 2020, , .		3
94	Hot-Electron Effects in AlGaN/GaN HEMTs Under Semi-ON DC Stress. IEEE Transactions on Electron Devices, 2020, 67, 4602-4605.	1.6	41
95	Geometric Modeling of Thermal Resistance in GaN HEMTs on Silicon. IEEE Transactions on Electron Devices, 2020, 67, 5408-5414.	1.6	4
96	Trapping and Detrapping Mechanisms in <i>Î²</i>-Gaâ„Oâ‚ƒ Vertical FinFETs Investigated by Electro-Optical Measurements. IEEE Transactions on Electron Devices, 2020, 67, 3954-3959.	1.6	24
97	Degradation mechanisms in high power InGaN semiconductor lasers investigated by electrical, optical, spectral and C-DLTS measurements. Microelectronics Reliability, 2020, 114, 113786.	0.9	0
98	Use of Bilayer Gate Insulator in GaN-on-Si Vertical Trench MOSFETs: Impact on Performance and Reliability. Materials, 2020, 13, 4740.	1.3	12
99	Exploration of gate trench module for vertical GaN devices. Microelectronics Reliability, 2020, 114, 113828.	0.9	6
100	Non thermally-activated transients and buffer traps in GaN transistors with p-type gate: A new method for extracting the activation energy. Microelectronics Reliability, 2020, 114, 113842.	0.9	3
101	A novel on-wafer approach to test the stability of GaN-based devices in hard switching conditions: Study of hot-electron effects. Microelectronics Reliability, 2020, 114, 113830.	0.9	10
102	Degradation mechanism of 0.15ÂÎ¼m AlGaN/GaN HEMTs: effects of hot electrons. Microelectronics Reliability, 2020, 114, 113905.	0.9	5
103	OFF-state trapping phenomena in GaN HEMTs: Interplay between gate trapping, acceptor ionization and positive charge redistribution. Microelectronics Reliability, 2020, 114, 113841.	0.9	6
104	Influence of CdTe solar cell properties on stability at high temperatures. Microelectronics Reliability, 2020, 114, 113847.	0.9	6
105	Reliability of H-terminated diamond MESFETs in high power dissipation operating condition. Microelectronics Reliability, 2020, 114, 113898.	0.9	3
106	Degradation of InGaN-based LEDs: Demonstration of a recombination-dependent defect-generation process. Journal of Applied Physics, 2020, 127, .	1.1	20
107	Thermal droop in III-nitride based light-emitting diodes: Physical origin and perspectives. Journal of Applied Physics, 2020, 127, .	1.1	54
108	Storage and release of buffer charge in GaN-on-Si HEMTs investigated by transient measurements. Applied Physics Express, 2020, 13, 074003.	1.1	8

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109	On-Wafer Fast Evaluation of Failure Mechanism of 0.25-<i>Î¼</i>m AlGaN/GaN HEMTs: Evidence of Sidewall Indiffusion. IEEE Transactions on Electron Devices, 2020, 67, 2765-2770.	1.6	2
110	Impact of Residual Carbon on Avalanche Voltage and Stability of Polarization-Induced Vertical GaN p-n Junction. IEEE Transactions on Electron Devices, 2020, 67, 3978-3982.	1.6	4
111	Modeling of gate capacitance of GaN-based trench-gate vertical metal-oxide-semiconductor devices. Applied Physics Express, 2020, 13, 024006.	1.1	7
112	Demonstration of Bilayer Gate Insulator for Improved Reliability in GaN-on-Si Vertical Transistors. , 2020, , .		1
113	Reliability Physics of GaN HEMT Microwave Devices: The Age of Scaling. , 2020, , .		7
114	Trap Dynamics Model Explaining the R_{ON} Stress/Recovery Behavior in Carbon-Doped Power AlGaN/GaN MOS-HEMTs. , 2020, , .		11
115	Modeling of the Vertical Leakage Current in AlN/Si Heterojunctions for GaN Power Applications. IEEE Transactions on Electron Devices, 2020, 67, 595-599.	1.6	10
116	Vertical Leakage in GaN-on-Si Stacks Investigated by a Buffer Decomposition Experiment. Micromachines, 2020, 11, 101.	1.4	3
117	Observation of I_D-V_D Kink in N-Polar GaN MIS-HEMTs at Cryogenic Temperatures. IEEE Electron Device Letters, 2020, 41, 345-348.	2.2	15
118	Understanding $gamma$ -Ray Induced Instability in AlGaN/GaN HEMTs Using a Physics-Based Compact Model. IEEE Transactions on Electron Devices, 2020, 67, 1126-1131.	1.6	11
119	Fast System to measure the dynamic onâ€resistance of onâ€wafer 600ÂV normally off GaN HEMTs in hardâ€switching application conditions. IET Power Electronics, 2020, 13, 2390-2397.	1.5	12
120	Carrier capture kinetics, deep levels, and isolation properties of <i>Î²</i> -Ga2O3 Schottky-barrier diodes damaged by nitrogen implantation. Applied Physics Letters, 2020, 117, .	1.5	20
121	Efficiency and Catastrophic Failure of High-Power Blue GaN LEDs During Extremely High Temperature and Current Stress. IEEE Transactions on Device and Materials Reliability, 2020, 20, 429-435.	1.5	3
122	Modeling the degradation mechanisms of AlGaN-based UV-C LEDs: from injection efficiency to mid-gap state generation. Photonics Research, 2020, 8, 1786.	3.4	27
123	Analysis of threshold voltage instabilities in semi-vertical GaN-on-Si FETs. Applied Physics Express, 2020, 13, 024004.	1.1	17
124	Analysis and design of extreme intensity irradiation devices for research applications. , 2020, , .		0
125	Role of defects in the mid-term degradation of UV-B LEDs investigated by optical and DLTS measurements. , 2020, , .		0
126	Degradation and recovery of high-periodicity InGaN/GaN MQWs under optical stress in short-circuit condition. , 2020, , .		0

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127	Demonstration of current-dependent degradation of quantum-dot lasers grown on silicon: role of defect diffusion processes. , 2020, , .		1
128	Degradation mechanisms of 1.6 W blue semiconductor lasers: effect on subthreshold optical power and power spectral density. , 2020, , .		0
129	Dependence of degradation on InGaN quantum well position: a study based on color coded structures. , 2020, , .		0
130	Charge trapping and degradation of Ga2O3 isolation structures for power electronics. , 2020, , .		0
131	GaN-based lateral and vertical devices: physical mechanisms limiting stability and reliability. , 2019, , .		3
132	Positive temperature dependence of time-dependent breakdown of GaN-on-Si E-mode HEMTs under positive gate stress. Applied Physics Letters, 2019, 115, .	1.5	25
133	Hot-Electron Effects in GaN GITs and HD-GITs: A Comprehensive Analysis. , 2019, , .		5
134	Influence of Gate Length on pBTI in GaN-on-Si E-Mode MOSc-HEMT. , 2019, , .		4
135	Threshold Voltage Instability Mechanisms in p-GaN Gate AlGaN/GaN HEMTs. , 2019, , .		36
136	Degradation processes of 280 nm high power DUV LEDs: impact on parasitic luminescence. Japanese Journal of Applied Physics, 2019, 58, SCCC19.	0.8	19
137	Top-down GaN nanowire transistors with nearly zero gate hysteresis for parallel vertical electronics. Scientific Reports, 2019, 9, 10301.	1.6	32
138	Impact of Sidewall Etching on the Dynamic Performance of GaN-on-Si E-Mode Transistors. , 2019, , .		3
139	Gate Stability and Robustness of In-Situ Oxide GaN Interlayer Based Vertical Trench MOSFETs (OG-FETs). , 2019, , .		1
140	Reliability comparison of AlGaN/GaN HEMTs with different carbon doping concentration. Microelectronics Reliability, 2019, 100-101, 113489.	0.9	7
141	Investigation into trapping modes and threshold instabilities of state-of-art commercial GaN HEMTs. Microelectronics Reliability, 2019, 100-101, 113464.	0.9	2
142	Breakdown Walkout in Polarization-Doped Vertical GaN Diodes. IEEE Transactions on Electron Devices, 2019, 66, 4597-4603.	1.6	9
143	Characterization of charge trapping mechanisms in GaN vertical Fin FETs under positive gate bias. Microelectronics Reliability, 2019, 100-101, 113488.	0.9	9
144	Linearity and robustness evaluation of 150-nm AlN/GaN HEMTs. Microelectronics Reliability, 2019, 100-101, 113388.	0.9	7

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145	Investigation of the degradations in power GaN-on-Si MIS-HEMTs subjected to cumulative Î³-ray irradiation. Microelectronics Reliability, 2019, 100-101, 113349.	0.9	3
146	High-Current Stress of UV-B (In)AlGaN-Based LEDs: Defect-Generation and Diffusion Processes. IEEE Transactions on Electron Devices, 2019, 66, 3387-3392.	1.6	24
147	Enhanced semiclassical simulation of InGaN/GaN multi-quantum-well solar cells. , 2019, , .		0
148	$mu s$-Range Evaluation of Threshold Voltage Instabilities of GaN-on-Si HEMTs with p-GaN Gate. , 2019, , .		13
149	Buffer breakdown in GaN-on-Si HEMTs: A comprehensive study based on a sequential growth experiment. Microelectronics Reliability, 2019, 100-101, 113461.	0.9	13
150	ESD-failure of E-mode GaN HEMTs: Role of device geometry and charge trapping. Microelectronics Reliability, 2019, 100-101, 113334.	0.9	13
151	Stability and degradation of isolation and surface in Ga2O3 devices. Microelectronics Reliability, 2019, 100-101, 113453.	0.9	6
152	Stability and degradation of AlGaN-based UV-B LEDs: Role of doping and semiconductor defects. Microelectronics Reliability, 2019, 100-101, 113418.	0.9	16
153	Gate Reliability of p-GaN Gate AlGaN/GaN High Electron Mobility Transistors. IEEE Electron Device Letters, 2019, 40, 379-382.	2.2	21
154	Perimeter Driven Transport in the p-GaN Gate as a Limiting Factor for Gate Reliability. , 2019, , .		27
155	Physical Origin of the Optical Degradation of InAs Quantum Dot Lasers. IEEE Journal of Quantum Electronics, 2019, 55, 1-7.	1.0	16
156	Evidence for defect-assisted tunneling and recombination at extremely low current in InGaN/GaN-based LEDs. Applied Physics Express, 2019, 12, 052007.	1.1	17
157	Demonstration of UV-Induced Threshold Voltage Instabilities in Vertical GaN Nanowire Array-Based Transistors. IEEE Transactions on Electron Devices, 2019, 66, 2119-2124.	1.6	5
158	Investigation of nBTI degradation on GaN-on-Si E-mode MOSc-HEMT. , 2019, , .		19
159	Reliability investigation on CdTe solar cells submitted to short-term thermal stress. Microelectronics Reliability, 2019, 100-101, 113490.	0.9	1
160	Hot-Electron Trapping and Hole-Induced Detrapping in GaN-Based GITs and HD-GITs. IEEE Transactions on Electron Devices, 2019, 66, 337-342.	1.6	22
161	Difluorochloromethane treated thin CdS buffer layers for improved CdTe solar cells. Thin Solid Films, 2019, 672, 7-13.	0.8	4
162	Analysis of magnesium zinc oxide layers for high efficiency CdTe devices. Thin Solid Films, 2019, 672, 22-25.	0.8	19

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163	The Effect of Proton Irradiation in Suppressing Current Collapse in AlGaN/GaN High-Electron-Mobility Transistors. IEEE Transactions on Electron Devices, 2019, 66, 372-377.	1.6	19
164	Reliability of Ultraviolet Light-Emitting Diodes. Solid State Lighting Technology and Application Series, 2019, , 397-424.	0.3	2
165	Origin of the low-forward leakage current in InGaN-based LEDs. , 2019, , .		0
166	Near-UV LED-based systems for low-cost and compact oxygen-sensing systems in gas and liquids. , 2019, , .		0
167	Degradation mechanisms of InAs quantum dot 1.3 um laser diodes epitaxially grown on silicon. , 2019, , .		0
168	Challenges for highly-reliable GaN-based LEDs. , 2019, , .		0
169	Degradation physics of GaN-based lateral and vertical devices. , 2019, , .		0
170	Evidence for avalanche generation in reverse-biased InGaN LEDs. , 2019, , .		0
171	2DEG Retraction and Potential Distribution of GaNâ€“onâ€“Si HEMTs Investigated Through a Floating Gate Terminal. IEEE Transactions on Electron Devices, 2018, 65, 1303-1307.	1.6	12
172	The 2018 GaN power electronics roadmap. Journal Physics D: Applied Physics, 2018, 51, 163001.	1.3	843
173	Chip-Level Degradation of InGaN-Based Optoelectronic Devices. Solid State Lighting Technology and Application Series, 2018, , 15-48.	0.3	0
174	Trapping phenomena and degradation mechanisms in GaN-based power HEMTs. Materials Science in Semiconductor Processing, 2018, 78, 118-126.	1.9	75
175	Positive and negative threshold voltage instabilities in GaN-based transistors. Microelectronics Reliability, 2018, 80, 257-265.	0.9	26
176	Impact of dislocations on DLTS spectra and degradation of InGaN-based laser diodes. Microelectronics Reliability, 2018, 88-90, 864-867.	0.9	4
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